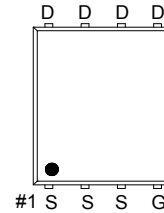
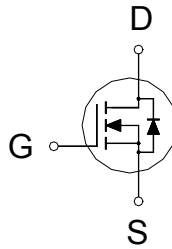




**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
40V	8m $\Omega$	42A



G. GATE  
D. DRAIN  
S. SOURCE

**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ }^\circ\text{C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	$I_D$	42	A
	$T_C = 100\text{ }^\circ\text{C}$		26.6	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	100	
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	$I_D$	11	
	$T_A = 70\text{ }^\circ\text{C}$		9	
Avalanche Current		$I_{AS}$	33.7	
Avalanche Energy	$L = 0.1\text{mH}$	$E_{AS}$	56.8	mJ
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	31	W
	$T_C = 100\text{ }^\circ\text{C}$		12.5	
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	$P_D$	2.3	W
	$T_A = 70\text{ }^\circ\text{C}$		1.5	
Operating Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	$^\circ\text{C}$

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient <sup>2</sup>	$R_{\theta JA}$		54	$^\circ\text{C} / \text{W}$
Junction-to-Case	$R_{\theta JC}$		4	

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25\text{ }^\circ\text{C}$ .

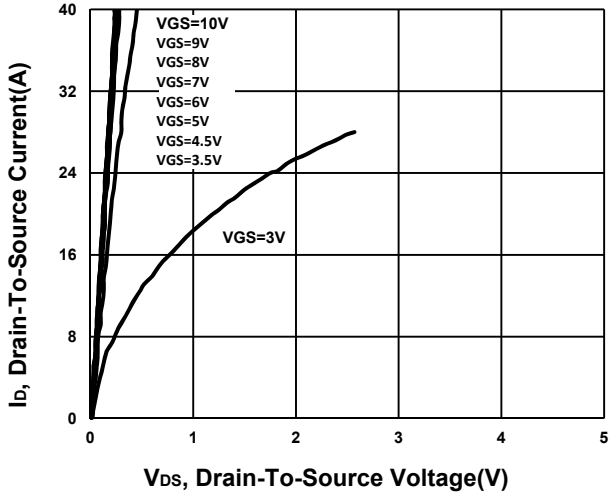
**ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25 °C, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	40			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.3	1.8	2.3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V			1	μA
		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 55 °C			10	
Drain-Source On-State Resistance <sup>1</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 11A		6.4	12	mΩ
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A		5.5	8	
Forward Transconductance <sup>1</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 11A		55		S
<b>DYNAMIC</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 15V, f = 1MHz		1672		pF
Output Capacitance	C <sub>oss</sub>			206		
Reverse Transfer Capacitance	C <sub>rss</sub>			124		
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1MHz		1.3		Ω
Total Gate Charge <sup>2</sup>	Q <sub>g</sub>	V <sub>GS</sub> = 10V	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A		34	nC
		V <sub>GS</sub> = 4.5V			18	
Gate-Source Charge <sup>2</sup>	Q <sub>gs</sub>			5.1		
Gate-Drain Charge <sup>2</sup>	Q <sub>gd</sub>			8.3		
Turn-On Delay Time <sup>2</sup>	t <sub>d(on)</sub>	V <sub>DS</sub> = 15V, I <sub>D</sub> ≅ 11A, V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 6Ω			25	
Rise Time <sup>2</sup>	t <sub>r</sub>			11		
Turn-Off Delay Time <sup>2</sup>	t <sub>d(off)</sub>			41		
Fall Time <sup>2</sup>	t <sub>f</sub>			12		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>J</sub> = 25 °C)</b>						
Continuous Current	I <sub>S</sub>				24	A
Forward Voltage <sup>1</sup>	V <sub>SD</sub>	I <sub>F</sub> = 11A, V <sub>GS</sub> = 0V			1.3	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 11A, dI <sub>F</sub> /dt = 100A / μS		19.5		nS
Reverse Recovery Charge	Q <sub>rr</sub>			9.4		nC

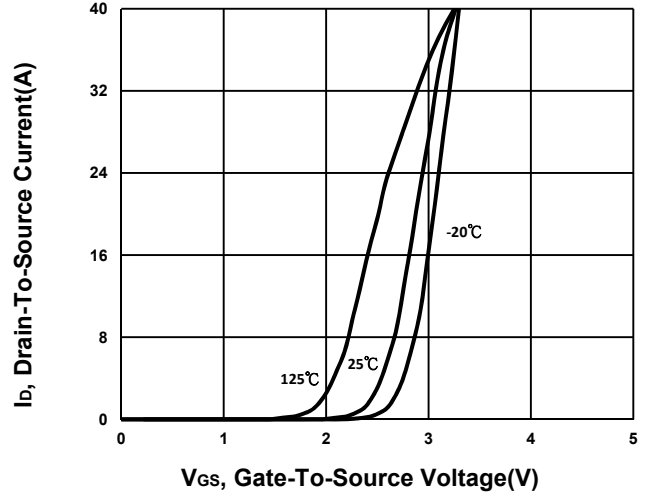
<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

<sup>2</sup>Independent of operating temperature.

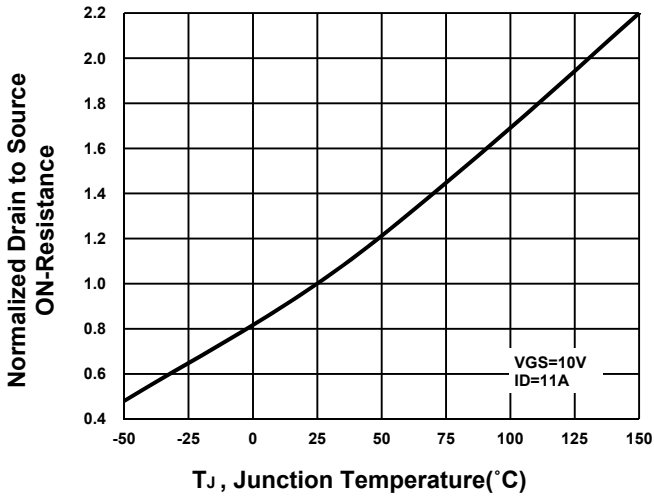
**Output Characteristics**



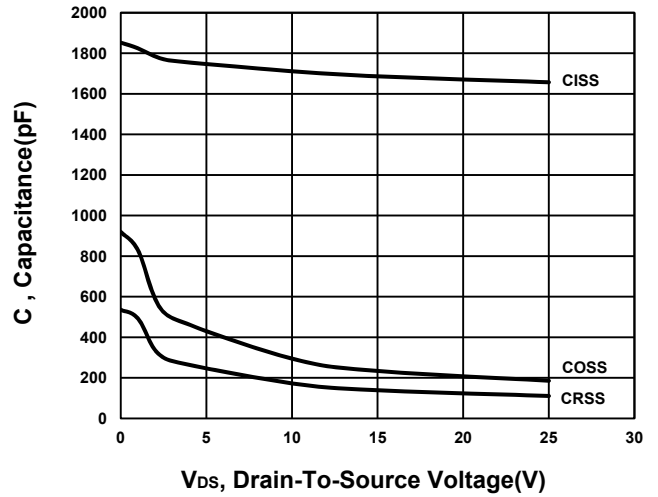
**Transfer Characteristics**



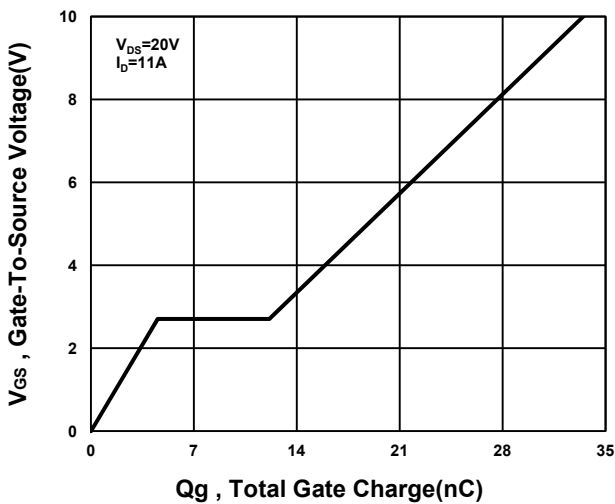
**On-Resistance VS Temperature**



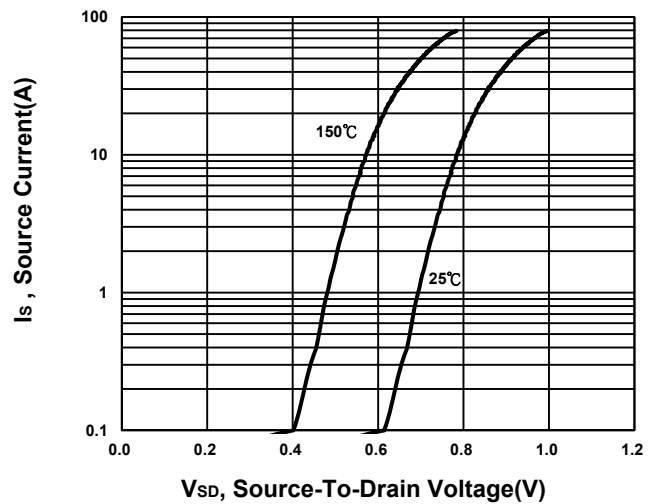
**Capacitance Characteristic**



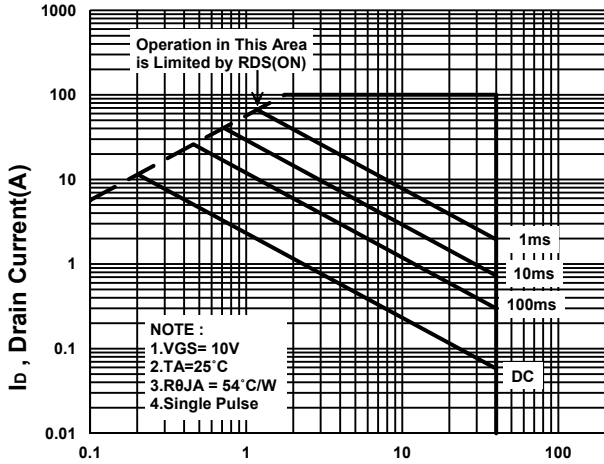
**Gate charge Characteristics**



**Source-Drain Diode Forward Voltage**

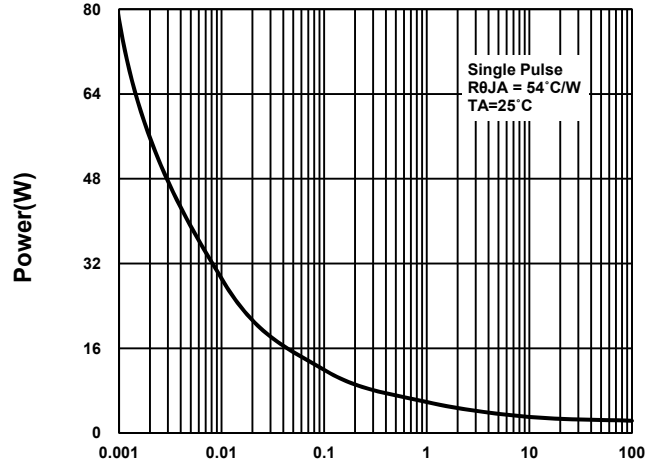


**Safe Operating Area**



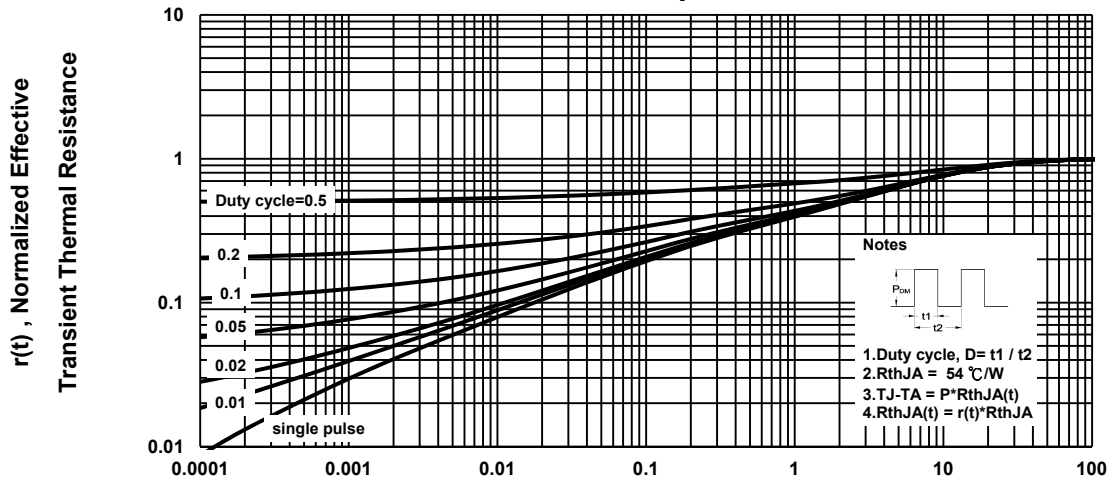
V<sub>DS</sub>, Drain-To-Source Voltage(V)

**Single Pulse Maximum Power Dissipation**



Single Pulse Time(s)

**Transient Thermal Response Curve**



T<sub>1</sub>, Square Wave Pulse Duration[sec]

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